TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

# 2 S A 1 1 4 5

## AUDIO FREQUENCY AMPLIFIER APPLICATIONS

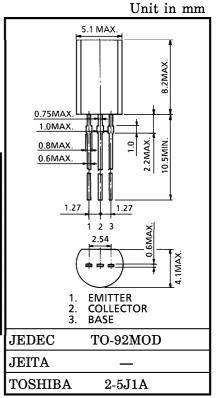
• Complementary to 2SC2705.

• Small Collector Output Capacitance :  $C_{ob} = 2.5 \text{ pF (Typ.)}$ 

• High Transition Frequency :  $f_T = 200 \text{ MHz}$  (Typ.)

# MAXIMUM RATINGS ( $Ta = 25^{\circ}C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	-150	V
Collector-Emitter Voltage	VCEO	-150	V
Emitter-Base Voltage	$V_{ m EBO}$	-5	V
Collector Current	$I_{\mathbf{C}}$	-50	mA
Base Current	$I_{B}$	-5	mA
Collector Power Dissipation	PC	800	mW
Junction Temperature	$T_{j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C



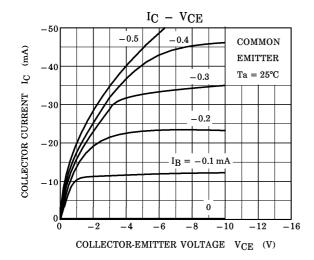
Weight: 0.36 g (Typ.)

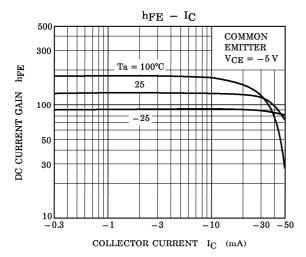
### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

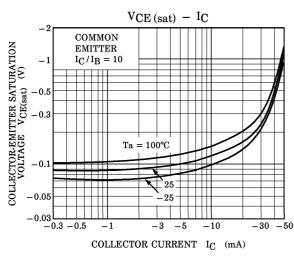
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{\mathrm{CBO}}$	$V_{CB} = -150 \text{ V}, I_{E} = 0$	_	_	-0.1	$\mu$ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	$\mu$ A
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	$I_{\mathrm{C}} = -1  \mathrm{mA},  I_{\mathrm{B}} = 0$	-150	_	_	V
DC Current Gain	hFE (Note)	$V_{ m CE} = -5   m V,  I_{ m C} = -10  mA$	80	_	240	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10  {\rm mA},  I_{\rm B} = -1  {\rm mA}$	_	_	-1.0	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$		_	-0.8	V
Transition Frequency	$ m f_{T}$	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	_	200	_	MHz
Collector Output Capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz	_	2.5	_	pF

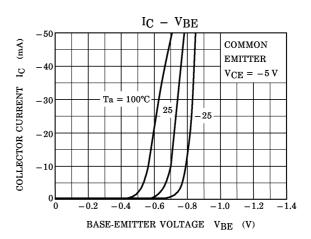
(Note): hFE Classification O: 80~160, Y: 120~240

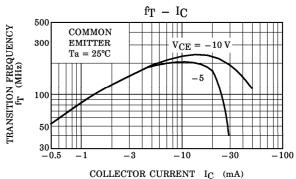
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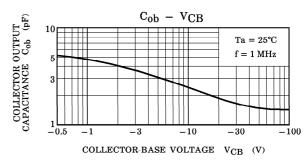


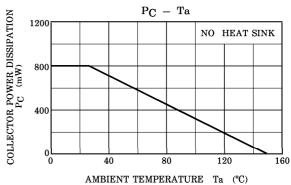












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